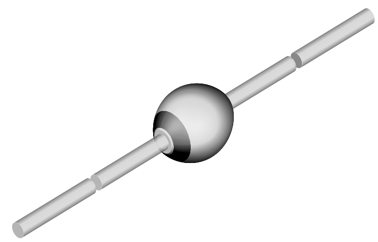
Standard Avalanche Sinterglass Diode

Features

- Controlled avalanche characteristics
- Glass passivated
- Low reverse current
- High surge current loading
- Hermetically sealed axial-leaded glass envelope
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



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Applications

Rectification diode, general purpose

Mechanical Data

Case: SOD-57 Sintered glass case

Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: approx. 369 mg

Parts Table

Part	Type differentiation	Package
1N5059	V_R = 200 V; I_{FAV} = 2 A	SOD-57
1N5060	V_R = 400 V; I_{FAV} = 2 A	SOD-57
1N5061	V_R = 600 V; I_{FAV} = 2 A	SOD-57
1N5062	V_R = 800 V; I_{FAV} = 2 A	SOD-57

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Reverse voltage = Repetitive peak reverse voltage	see electrical characteristics	1N5059	$V_R = V_{RRM}$	200	V
		1N5060	$V_R = V_{RRM}$	400	V
		1N5061	$V_R = V_{RRM}$	600	V
		1N5062	$V_R = V_{RRM}$	800	V
Peak forward surge current	t_p = 10 ms, half-sinewave		I_{FSM}	50	A
Average forward current	R_{thJA} = 45 K/W, T_{amb} = 50 °C		I_{FAV}	2	A
	R_{thJA} = 100K/W, T_{amb} = 75 °C		I_{FAV}	0.8	A
Junction and storage temperature range			$T_j = T_{stg}$	- 55 to + 175	°C
Max. pulse energy in avalanche mode, non repetitive (inductive load switch off)	$I_{(BR)R}$ = 1 A, indicutive load		E_R	20	mJ

Maximum Thermal Resistance

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction ambient	Lead length l = 10 mm, T_L = constant	R_{thJA}	45	K/W
	on PC board with spacing 25 mm	R_{thJA}	100	K/W

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	I_F = 1 A		V_F			1	V
	I_F = 2.5 A		V_F			1.15	V
Reverse current	$V_R = V_{RRM}$		I_R			1	μA
	$V_R = V_{RRM}$, T_j = 100 °C		I_R			10	μA
	$V_R = V_{RRM}$, T_j = 150 °C		I_R			100	μA
Reverse breakdown voltage	I_R = 100 μA	1N5059	$V_{(BR)R}$	225		1600	V
		1N5060	$V_{(BR)R}$	450		1600	V
		1N5061	$V_{(BR)R}$	650		1600	V
		1N5062	$V_{(BR)R}$	900		1600	V
Reverse recovery time	I_F = 0.5 A, I_R = 1 A, i_R = 0.25 A		t_{rr}			4	μs
Diode capacitance	V_R = 0 V, f = 1 MHz		C_D		40		pF

Typical Characteristics (Tamb = 25 °C unless otherwise specified)

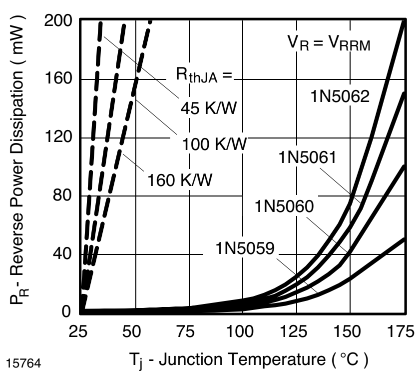


Figure 1. Max. Reverse Power Dissipation vs. Junction Temperature

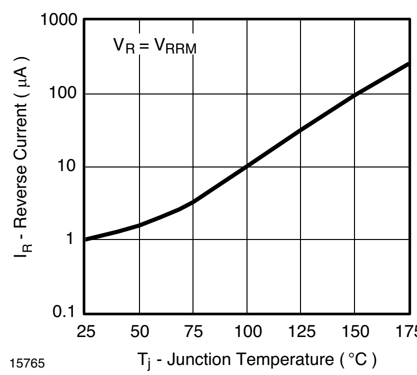


Figure 2. Max. Reverse Current vs. Junction Temperature

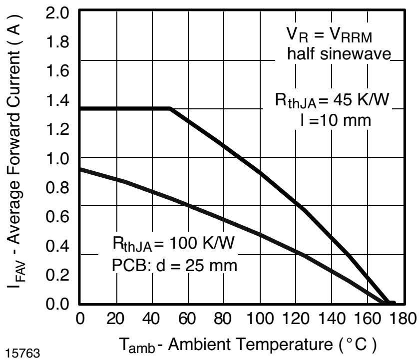


Figure 3. Max. Average Forward Current vs. Ambient Temperature

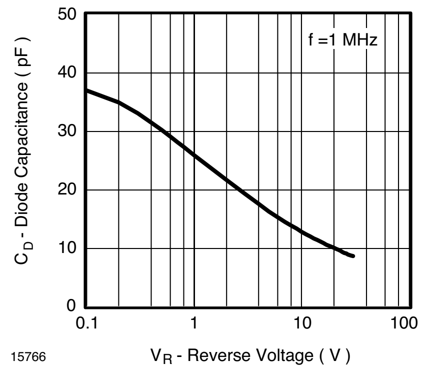


Figure 5. Typ. Diode Capacitance vs. Reverse Voltage

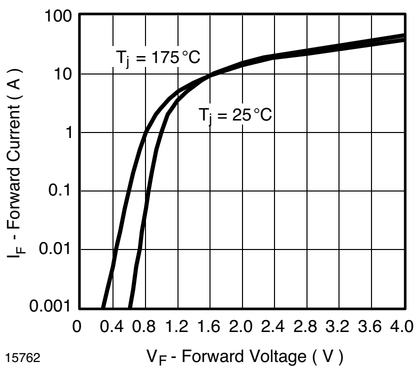
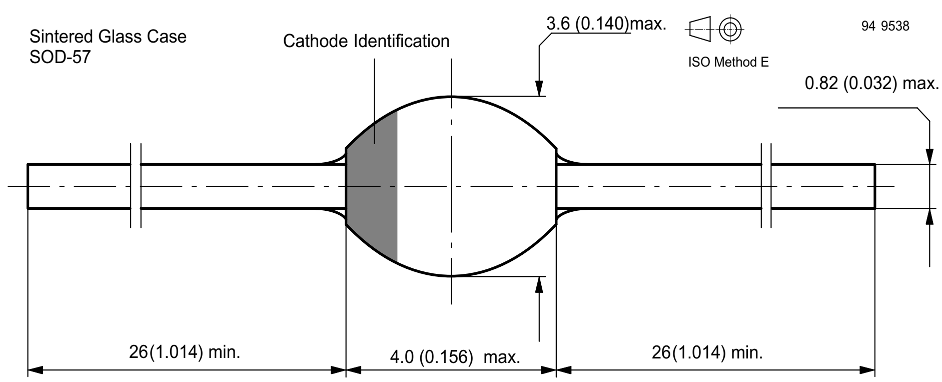


Figure 4. Max. Forward Current vs. Forward Voltage

Package Dimensions in mm (Inches)



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It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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